

Fig. 1 – PRIOR ART

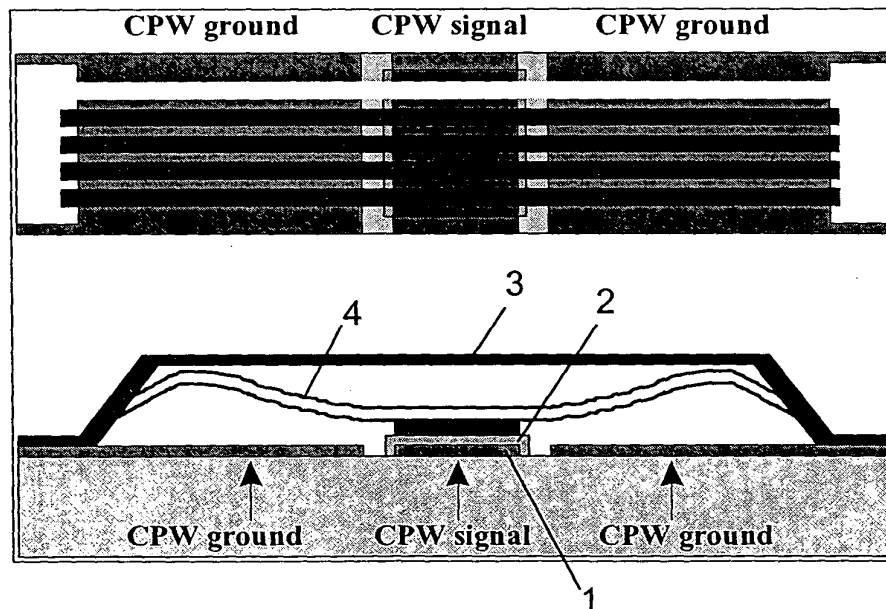
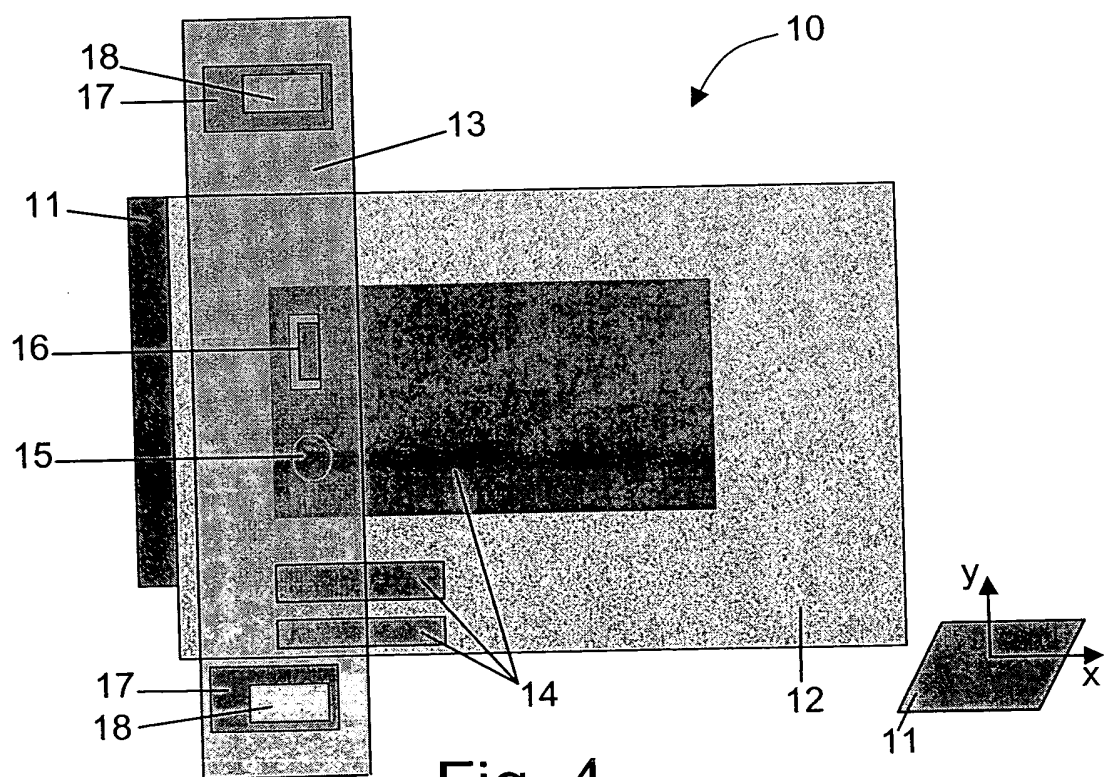
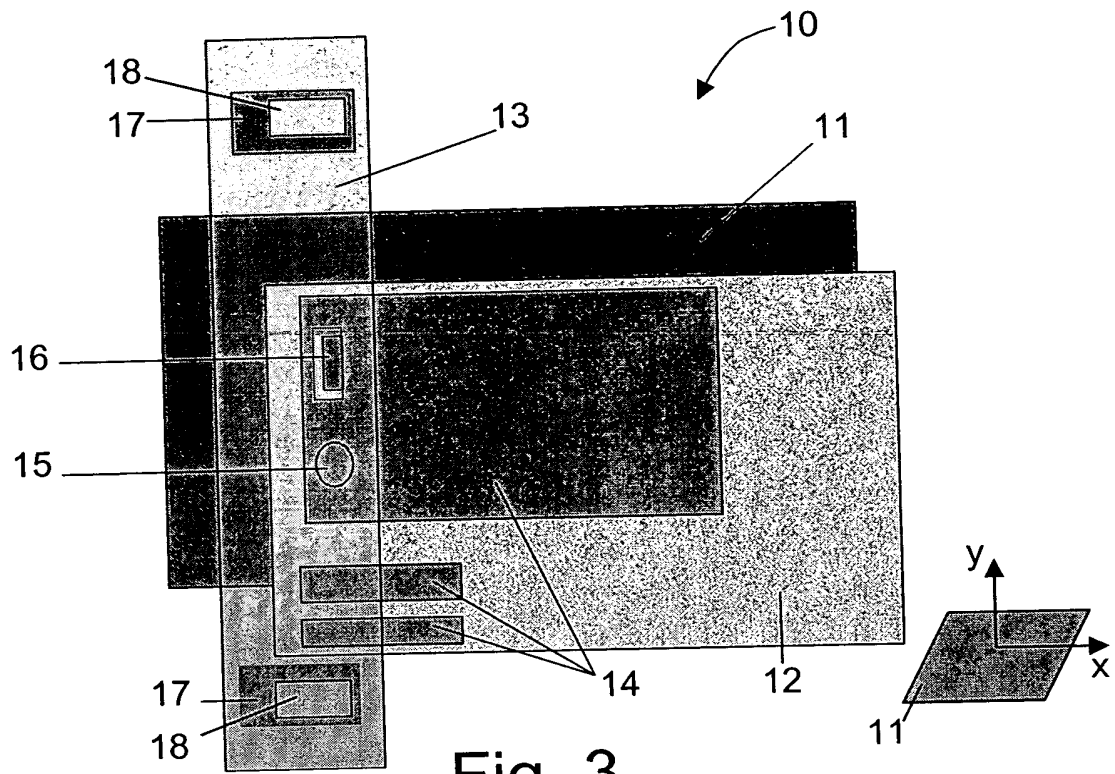
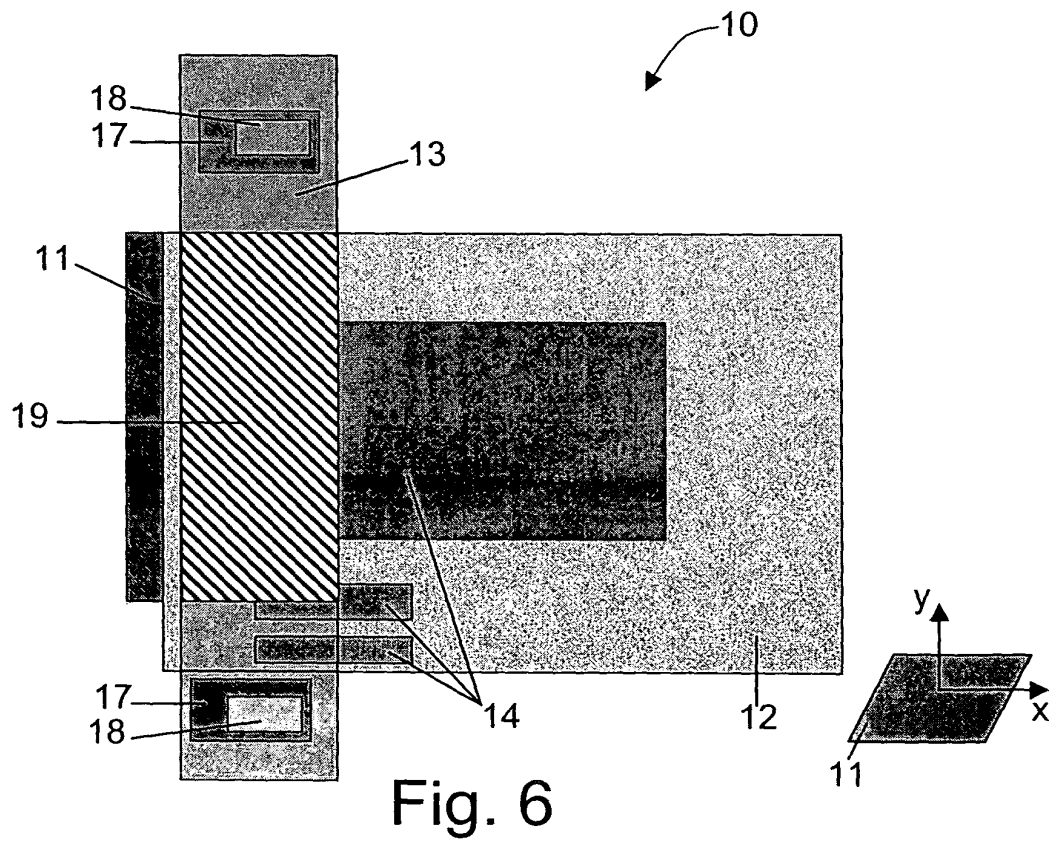
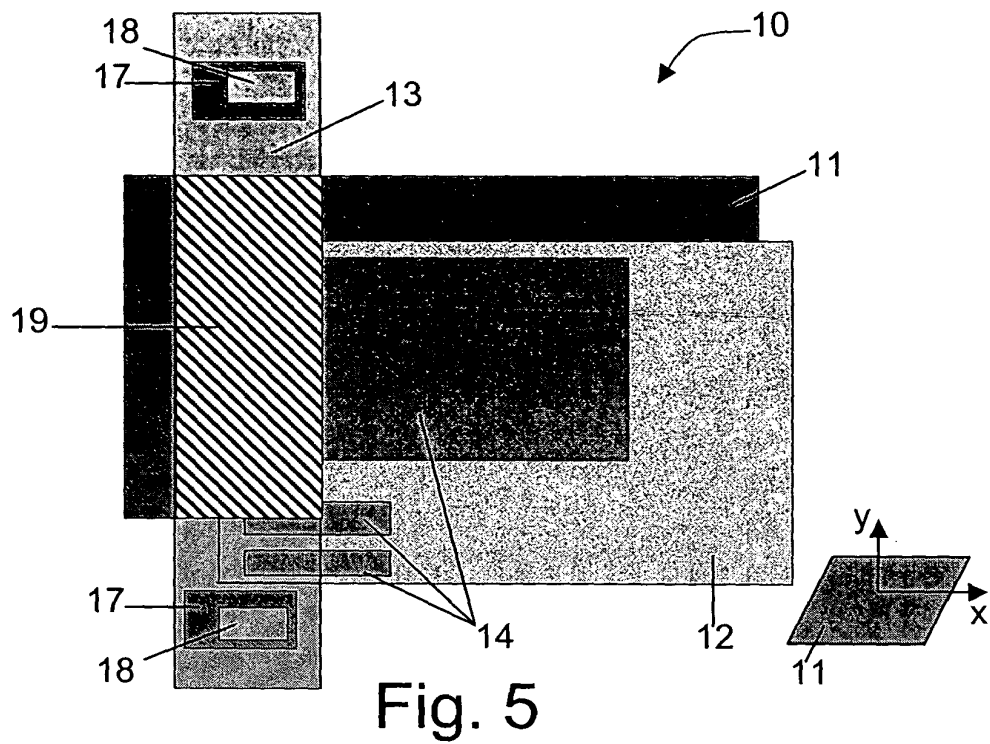
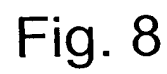
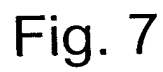
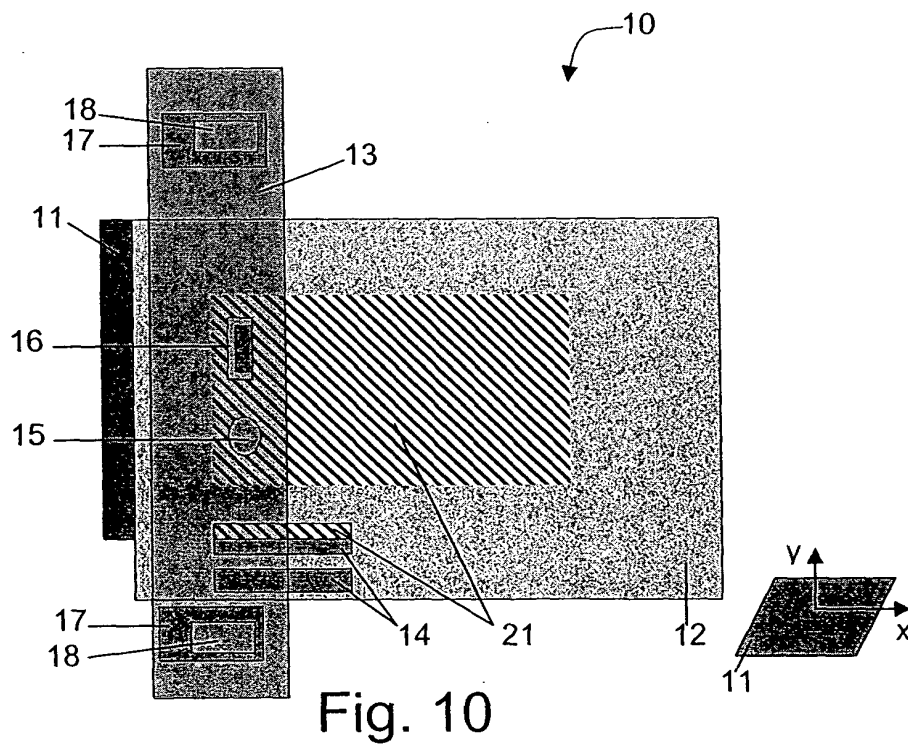
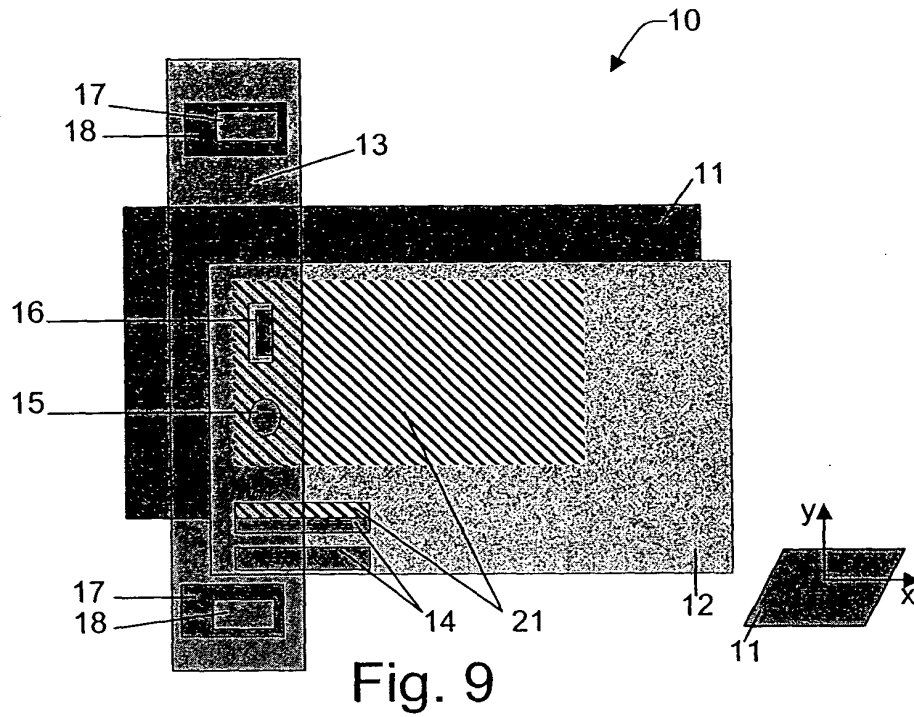


Fig. 2 – PRIOR ART









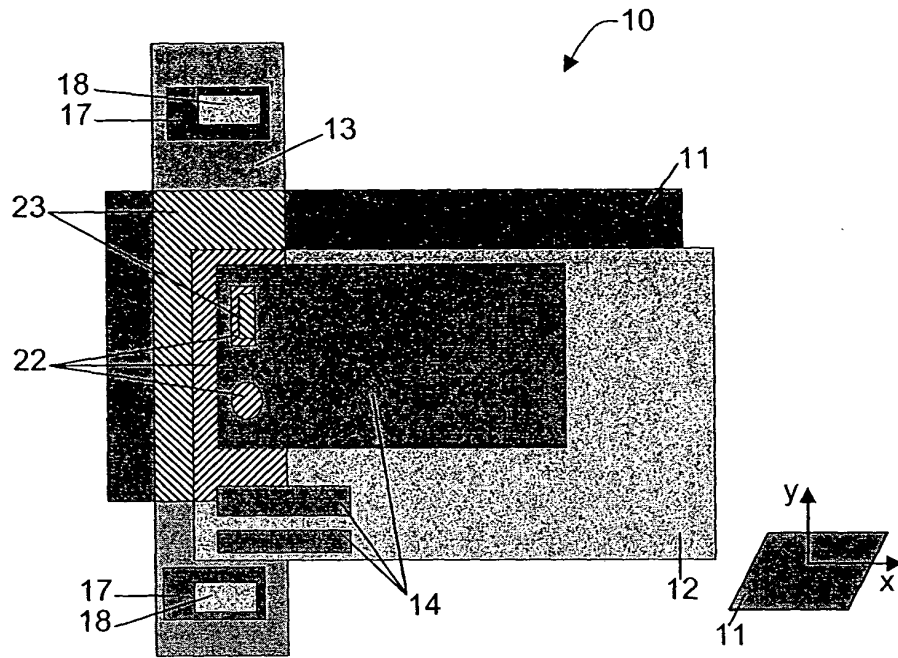


Fig. 11

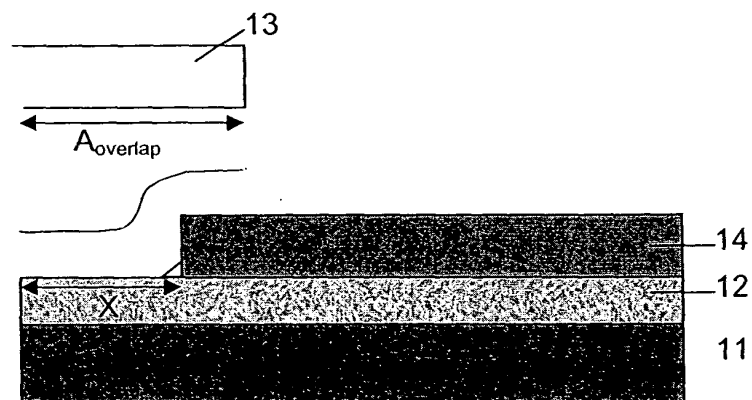
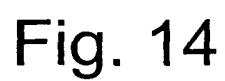
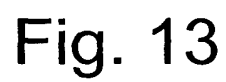


Fig. 12



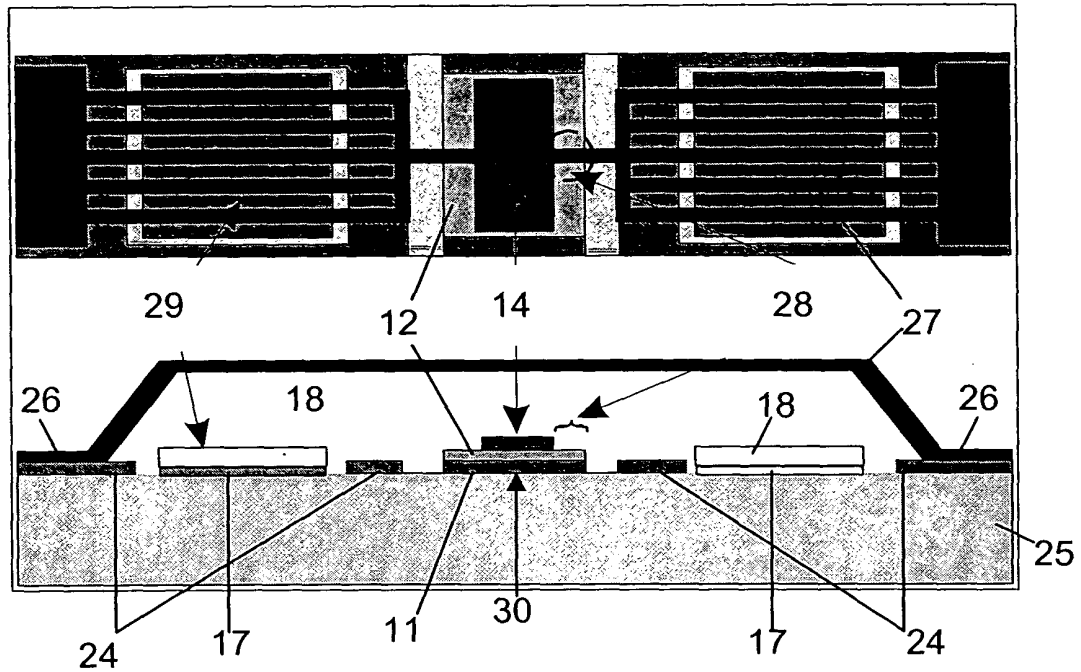


Fig. 15

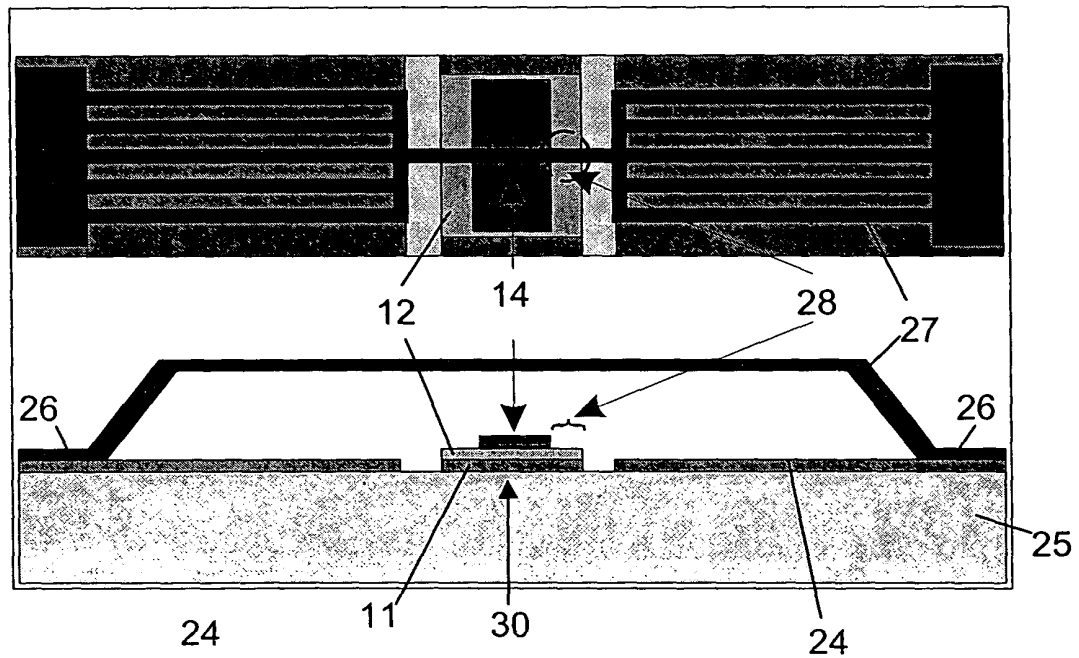


Fig. 16

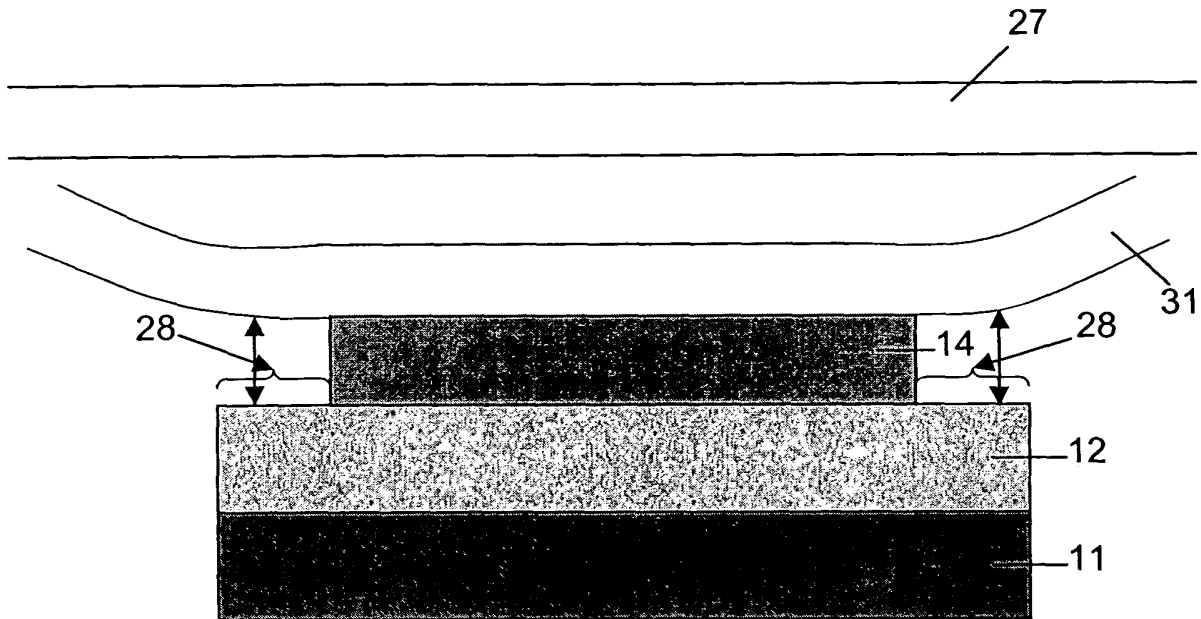


Fig. 17

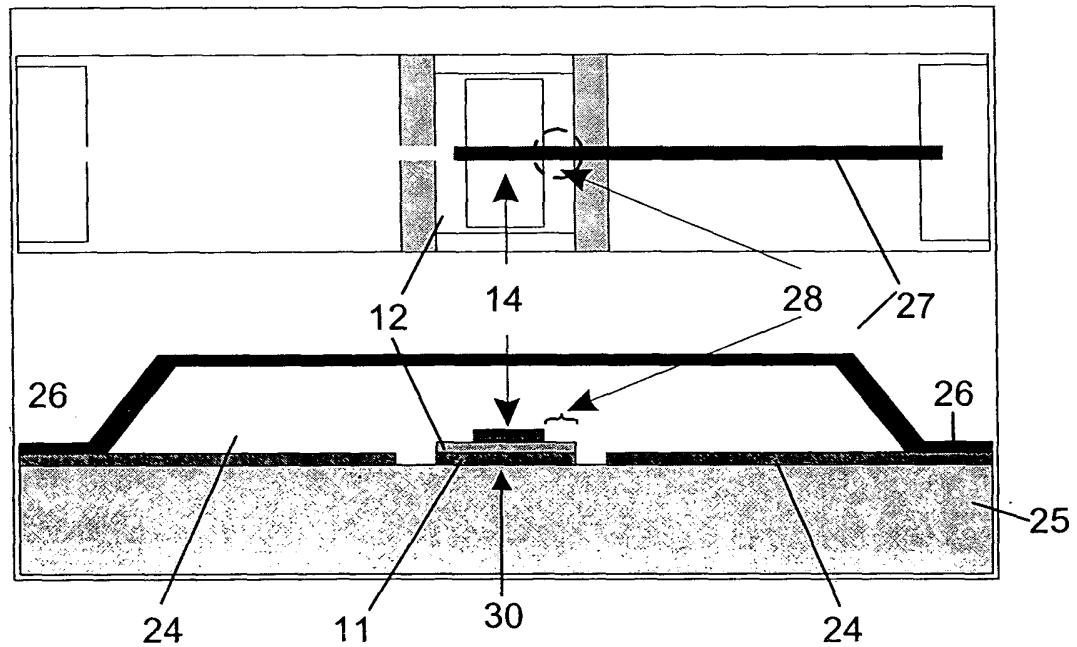


Fig. 18

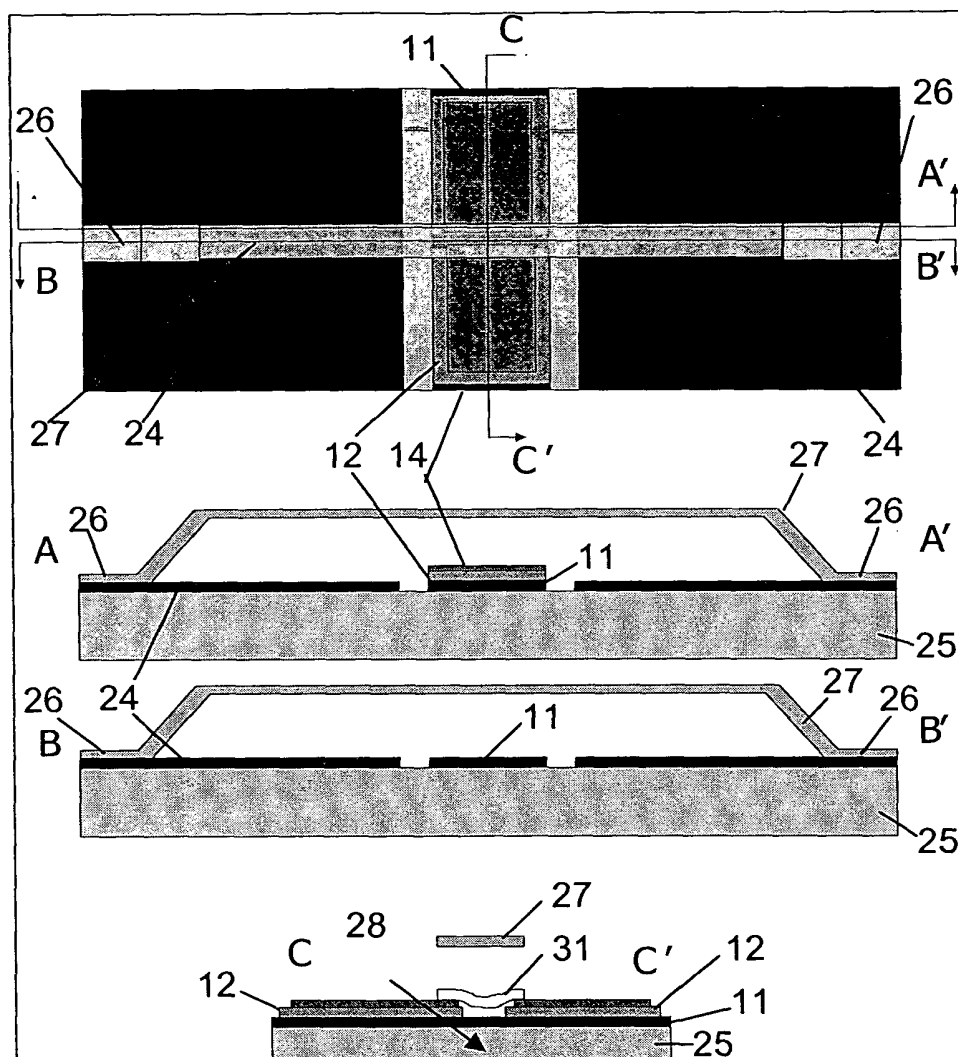


Fig. 19

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Figure 1 consists of three cross-sectional views of a semiconductor device. View (A) is a top view showing a central region 11, a surrounding region 12, and a substrate 25. View (B) is a side view showing a central region 11, a surrounding region 12, and a substrate 25. View (C) is a detail view of the central region 11, showing a central layer 31a and side layers 31b.

Fig. 20

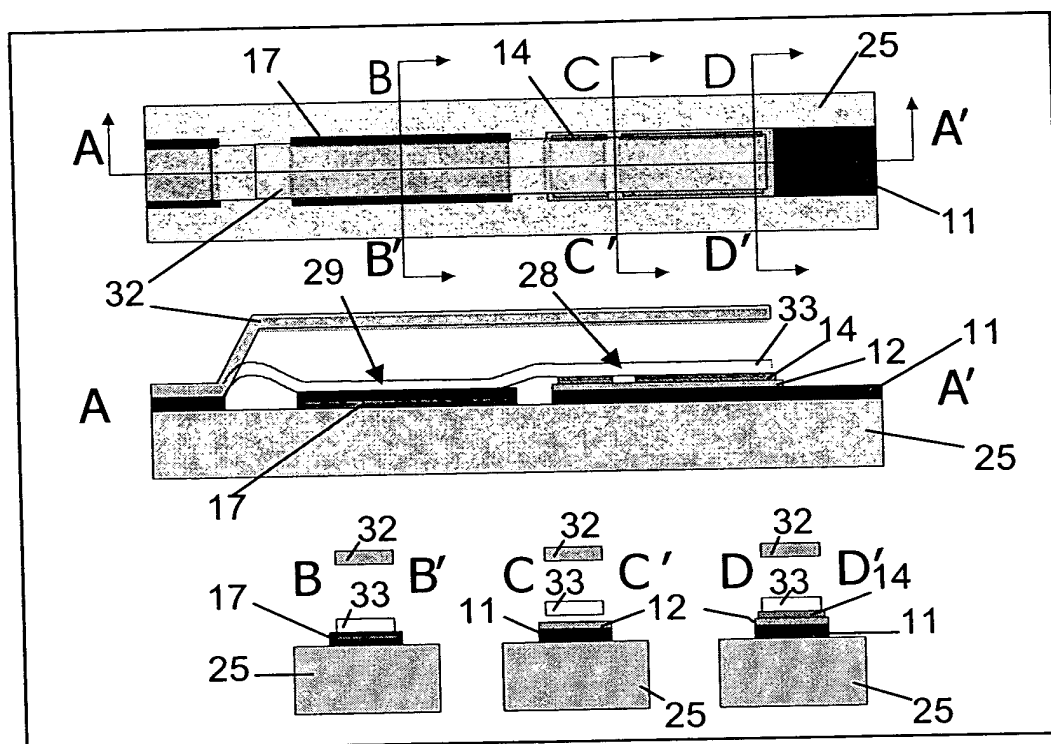


Fig. 21

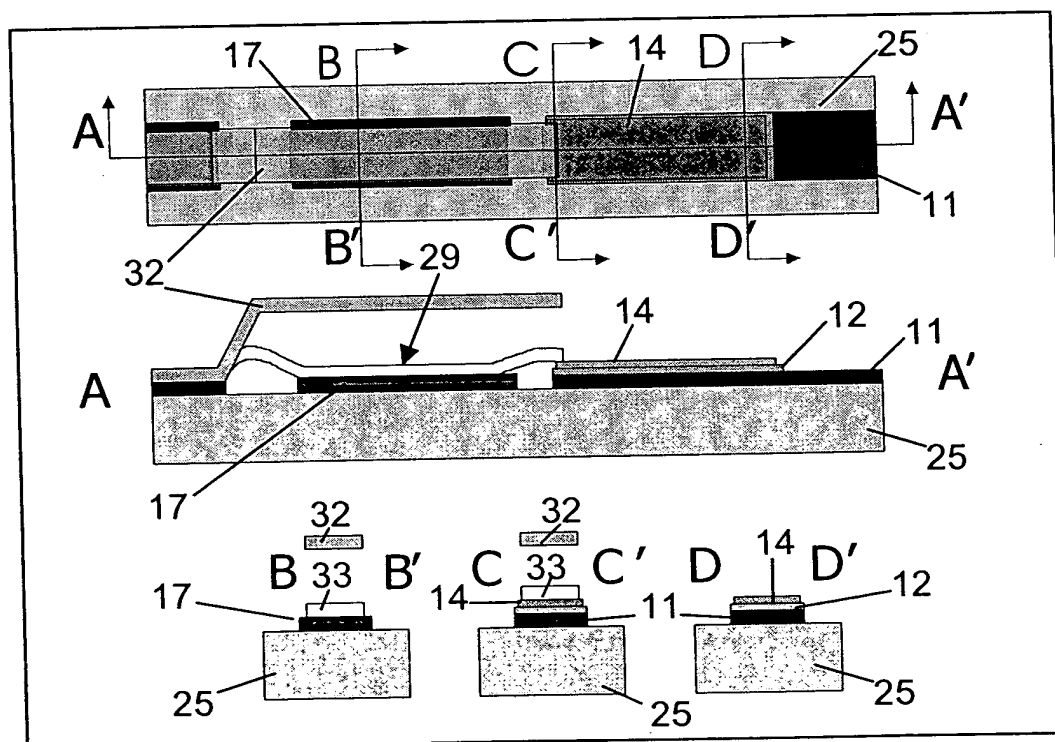


Fig. 22

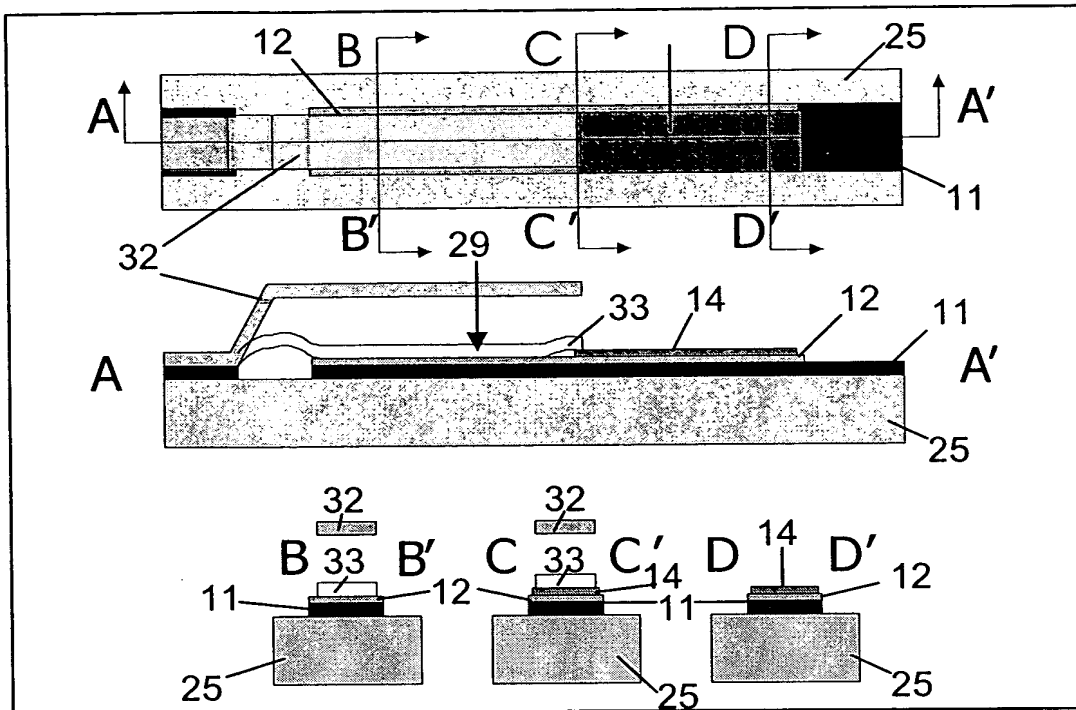


Fig. 23

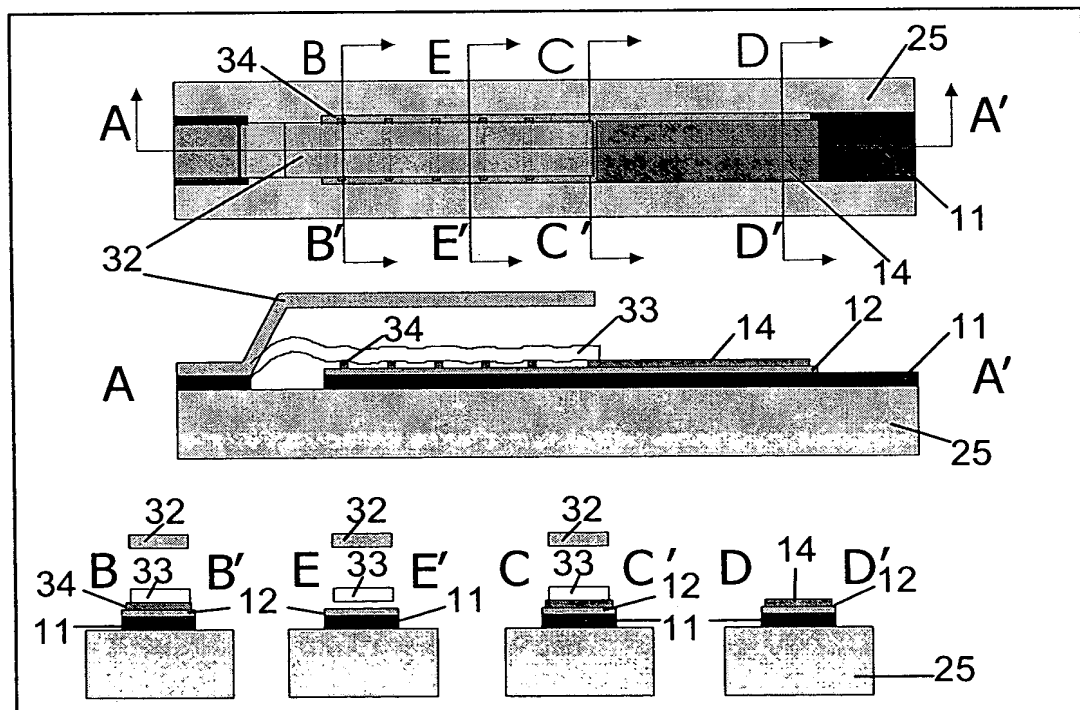


Fig. 25

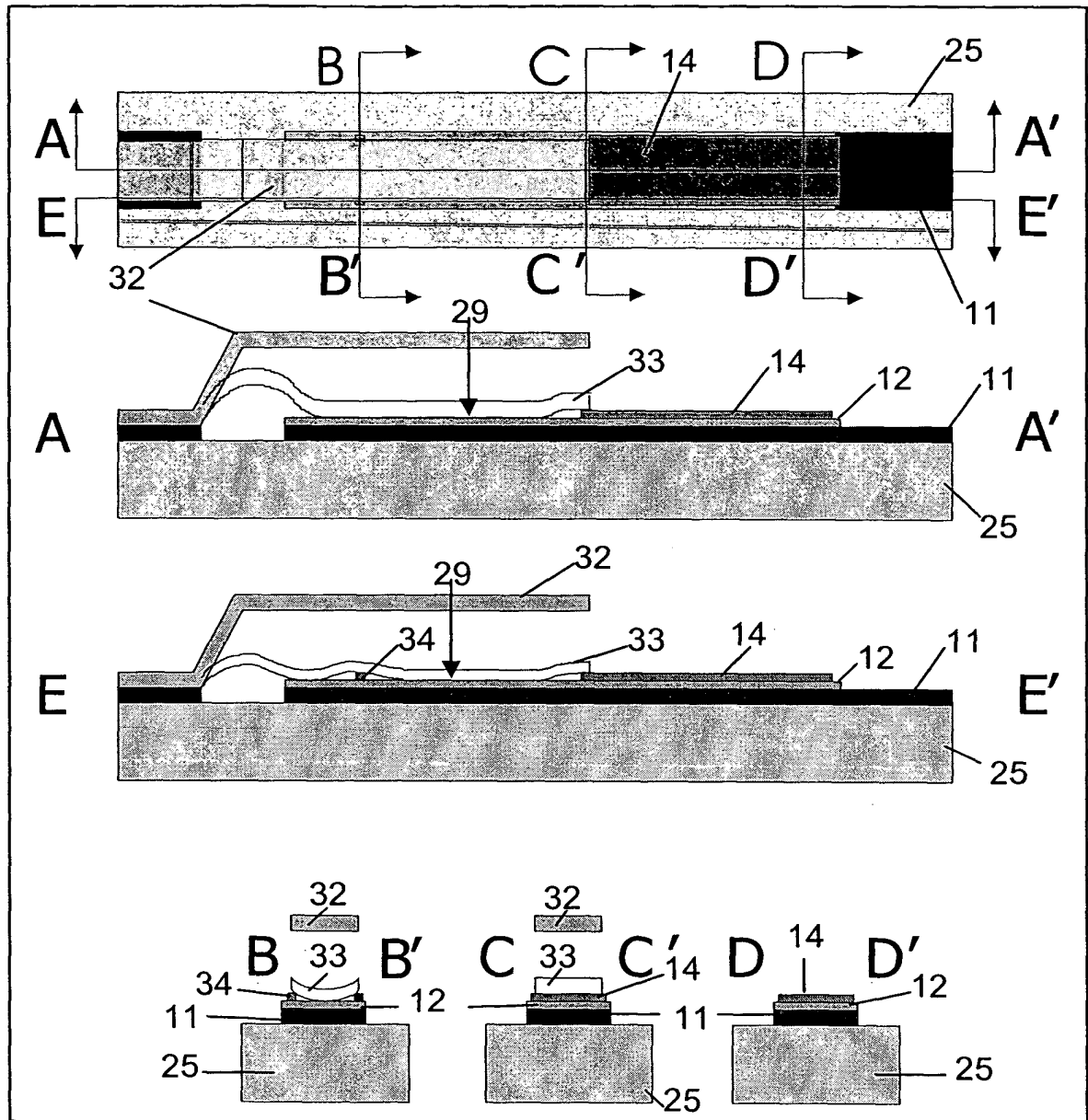


Fig. 24